

ESE 2025

Main Examination

UPSC ENGINEERING SERVICES EXAMINATION

Topicwise
**Conventional
Practice Questions**

Electrical Engineering

PAPER-I





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ESE Main Examination • Conventional Practice Questions : Electrical Engineering PAPER-I

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1

Electrical Materials

1. Crystallography

Level-1

1.1 Derive atomic packing factor for face centered cubic structure?

(10 Marks)

Solution:

In FCC structure, one atom lies at each corner of the cube. In addition to that one atom lies at the centre of each face.

So effective number of atoms per unit cell will be

$$N = \frac{1}{8} \times 8 + \frac{1}{2} \times 6 = 4$$

$$\therefore N = 4$$

In 2-dimension FCC structure can be drawn as shown in figure.

\therefore atomic radius of FCC is r .

$$AC^2 = AB^2 + BC^2$$

$$\therefore (r + 2r + r)^2 = a^2 + a^2$$

$$\therefore 16r^2 = 2a^2$$

$$\therefore r = \frac{\sqrt{2}a}{4}$$

Calculation of APF for FCC :

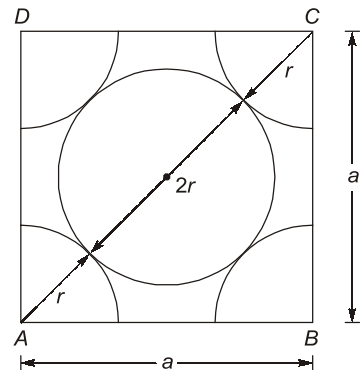
$$\text{APF} = \frac{\text{Sum of atomic volume in a unit cell}}{\text{Volume of a unit cell}}$$

$$= \frac{N \times \frac{4}{3} \pi r^3}{a^3}$$

$$= \frac{4 \times \frac{4}{3} \pi \left(\frac{\sqrt{2}a}{4} \right)^3}{a^3}$$

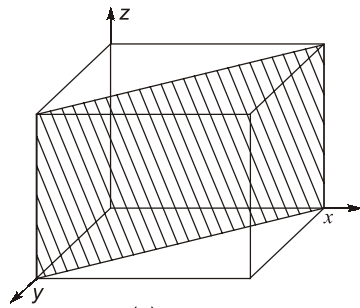
$$\text{APF} = 0.74$$

\therefore Atomic Packing Factor = 0.74 or 74%.

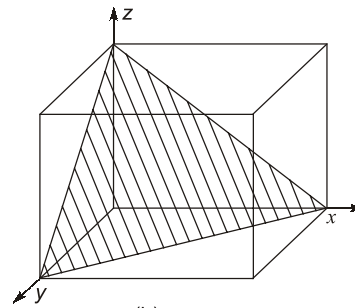


1.2 Find Miller indices of the following crystal structures?

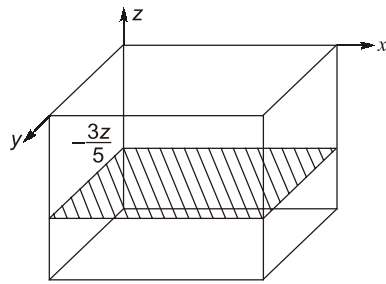
(10 Marks)



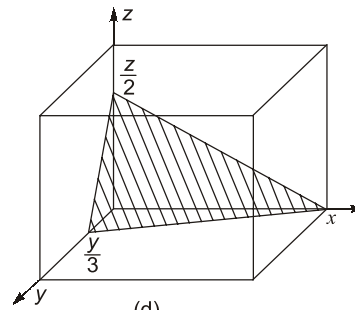
(a)



(b)



(c)



(d)

Solution:

(a) Intercepts :	x	y	z
Expressed in terms of unit cell dimension :	1	1	∞
Reciprocal :	1	1	0
Reduce reciprocal to smallest integer :	1	1	0
\therefore Miller indices =	[1 1 0]		
(b) Intercepts :	x	y	z
Expressed in terms of unit cell dimension :	1	1	1
Reciprocal :	1	1	1
Reduce reciprocal to smallest integer :	1	1	1
\therefore Miller indices =	[1 1 1]		
(c) Intercepts :	∞	∞	$-\frac{3}{5}z$
Expressed in terms of unit cell dimension :	∞	∞	$-\frac{3}{5}$
Reciprocal :	0	0	$-\frac{5}{3}$
Reduce reciprocal to smallest integer :	0	0	-5
\therefore Miller indices =	[0 0 $\bar{5}$]		
(d) Intercepts :	x	$\frac{y}{3}$	$\frac{z}{2}$

Expressed in terms of unit cell dimension : 1 $\frac{1}{3}$ $\frac{1}{2}$

Reciprocal : 1 3 2

Reduce reciprocal to smallest integer : 1 3 2

\therefore Miller indices = [1 3 2]

- 1.3 (i) Derive relation for atomic radius of unit cell for BCC crystal system and FCC crystal system.
 (ii) Enumerate different type of physical properties which get affected by structural imperfection in a crystal. Explain briefly about different types of point defects and line defects. (12 Marks)

Solution:

- (i) In body centered cubic structure, the atoms touch each other along the diagonal of the cube as shown in figure. Therefore, the length of the diagonal of cube is $4r$.

$$AC = \sqrt{AB^2 + BC^2}$$

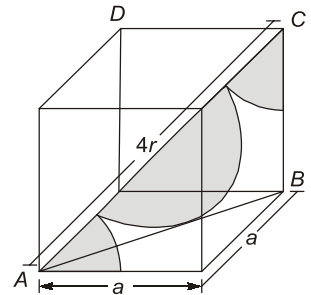
$$AB = \sqrt{x^2 + x^2} = x\sqrt{2}$$

$$BC = x \quad (\text{Let } a = x)$$

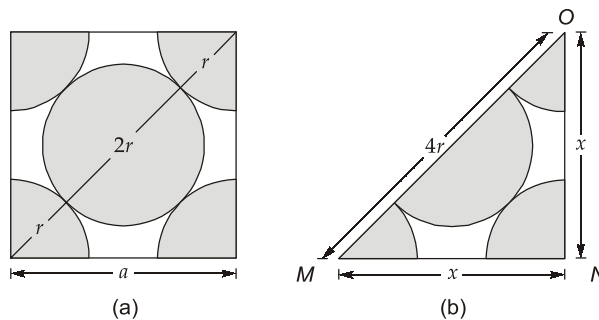
$$AC = 4r = \sqrt{(x\sqrt{2})^2 + x^2} = x\sqrt{3}$$

$$r = \frac{x\sqrt{3}}{4}$$

$$x = \frac{4r}{\sqrt{3}}$$



In face centered cubic structure, the atoms touch each other along the diagonal of any face of the cube as shown in figure. The length of the diagonal of the face = $4r$ as shown in figure below,



$$MO^2 = MN^2 + ON^2$$

$$(4r)^2 = x^2 + x^2 = 2x^2$$

or, $x = \frac{4r}{\sqrt{2}}$

or, $r = \frac{x\sqrt{2}}{4}$

or, $r^2 = \frac{2x^2}{16} = \frac{x^2}{8}$

$$r = \frac{x}{2\sqrt{2}}$$

So, $x = 2\sqrt{2}r$

- (ii) Imperfections result due to deviation from an orderly periodic array. The study of defect is especially useful when studying the properties of materials which are structure sensitive.

This affects the properties like fracture strength plasticity, electrical resistivity and thermal conduction.

Point Defects:

A point defect is a very localized defect in the regularity of a lattice and usually does not spread over more than one or two lattice spacing. The structural point defect can be classified into three types, i.e., vacancies, interstitial, and impurities.

- Vacancies defect: In vacancies defect, there may be missing atom in a crystal. A vacancy may result because of imperfect packing during original crystallization or may arise from thermal vibrations of atoms at elevated temperature.
- Interstitial defect: In interstitial defect, an atom occupies a definite position in the lattice such that it is normally not occupied in a perfect crystal. The position occupied by a normal atom or a foreign atom lies between the atoms of the ideal crystal.
- Impurity defect: In impurity defect, foreign atoms are introduced into a crystal lattice either as an interstitial atom or as a substitution atom. Therefore defects may be classified as interstitial impurity defect and substitution impurity defect.

Line Defects:

Line defects are basically one-dimensional defects or dislocations. Due to dislocations, lattice distortions are centered around a line. Dislocations are produced due to solidification of the crystalline solids by vacancy condensation or by atomic mismatch in the solid solutions. Dislocations are mainly of two types i.e., the edge dislocation and the screw dislocation.

- Edge dislocation: In edge dislocation an extra half plane of atoms is inserted in a crystal either above or below the slip plane. Edge dislocation may be either positive or negative.
- Screw dislocation: The screw dislocation can be created in a perfect crystal by applying upward or downward shear stresses to the regions of perfect crystal, which have been separated by a cutting plane. Screw dislocation may be either positive or negative.

- 1.4 When an NaCl crystal is subjected to an electric field of 1000 V/m, the resulting polarization is $4.3 \times 10^{-8} \text{ C/m}^2$. Calculate the relative permittivity of NaCl.

(10 Marks)

Solution:

Polarization,

$$P = \epsilon_0(\epsilon_r - 1)E$$

$$\epsilon_r = 1 + \frac{P}{\epsilon_0 E} = 1 + \frac{4.3 \times 10^{-8} \text{ C/m}^2}{(8.854 \times 10^{-12} \text{ F/m})(1000 \text{ V/m})}$$

$$\epsilon_r \approx 5.86$$

Level-2

- 1.5 The copper crystal has FCC unit cell configuration. If radius of Cu atom is 0.148 nm and atomic mass of Cu is 63.5 gmol^{-1} then calculate atomic packing fraction (APF), the atomic concentration in a unit cell and density of Cu atom in gcm^{-3} .

(Take Avogadro number : $6.023 \times 10^{23} \text{ mol}^{-1}$)

(15 Marks)

Solution:

For the given material (Cu),

$$\text{Atomic packing fraction, (APF)} = \frac{(\text{No. of atom in unit cell}) \times \text{Volume of atom}}{\text{Volume of unit cell}}$$

For face centred cubic unit cell = 4

$$\text{Volume of an atom} = \frac{4}{3}\pi R^3$$

$$\text{Volume of unit cell} = a^3$$

Where,

R is radius of copper atom

a is the cube side length

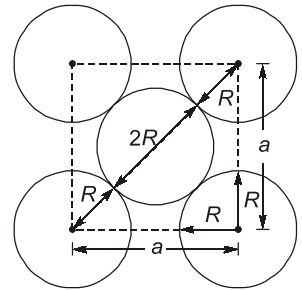
$$\text{APF} = \frac{4 \times \frac{4}{3}\pi R^3}{a^3} = \frac{\frac{4^2}{3}\pi R^3}{(2\sqrt{2}R)^3}$$

Face section of unit cell,

As,

$$a = 2\sqrt{2}R$$

$$\text{APF} = \frac{4^2\pi}{3(2\sqrt{2})^3} = 0.7404$$



Assuming there are x atoms in unit cell,

$$\text{Atomic concentration, } n_{\text{at}} = \frac{\text{No. of atoms in unit cell}}{\text{Volume of unit cell}} = \frac{x}{a^3}$$

$$\begin{aligned} n_{\text{at}} &= \frac{4}{(2\sqrt{2}R)^3} = \frac{4}{(2\sqrt{2} \times 0.148 \times 10^{-9})^3} \\ &= \frac{4}{(4.186 \times 10^{-10})^3} = 5.453 \times 10^{28} \text{ m}^{-3} = 5.453 \times 10^{22} \text{ cm}^{-3} \end{aligned}$$

$$\text{The density of copper, } \rho = \frac{\text{Mass of all atoms in unit cell}}{\text{Volume of unit cell}}$$

$$= \frac{x \left(\frac{M_{\text{at}}}{N_A} \right)}{a^3} \quad (\text{Where } M_{\text{at}} \text{ is atomic mass of Cu})$$

\therefore

$$\begin{aligned} \rho &= \frac{n_{\text{at}} M_{\text{at}}}{N_A} = \frac{5.453 \times 10^{22} \times 63.5 \text{ gmmol}^{-1}}{6.023 \times 10^{23} \text{ mol}^{-1}} \\ &= 5.749 \text{ gm cm}^{-3} \end{aligned}$$

1.6 What are the types of cubic crystal structure? Derive the atomic packing factor of all the cubic crystal structures.

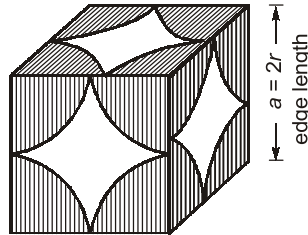
(20 Marks)

Solution:

There are three types of cubic crystal structures:

- **Simple Cubic Crystal structure (SCC):**

In this structure, there is one Lattice point at each of the eight corners of the unit cell. It has a coordination number of six.



Atomic Packing Factor (APF) of the crystal structure is defined as the ratio of total volume of the atoms per unit cell to the volume of the unit cell. It is also known as packing efficiency (η)

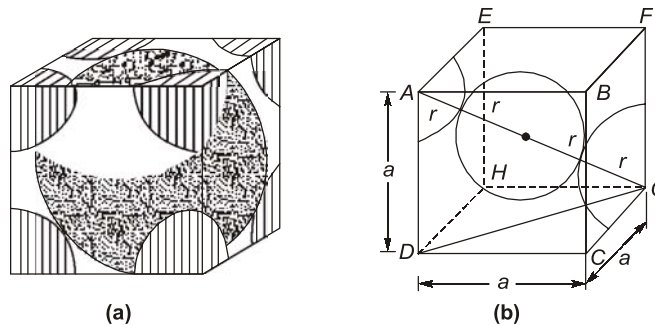
Here,

$$\text{APF} = \frac{1 \times (\pi/6) a^3}{a^3} = \frac{\pi}{6} = 0.524$$

\therefore % APF = 52.4% filled

- **Body Centered Cubic structure (BCC):**

In this structure, in an unit cell there are eight atoms at corners and another atom is at the body center. It has a coordination number of eight.



Body centered cubic structure

From the figure,

$$r = \frac{a\sqrt{3}}{4}$$

and for BCC,

$$N = 2$$

Now,

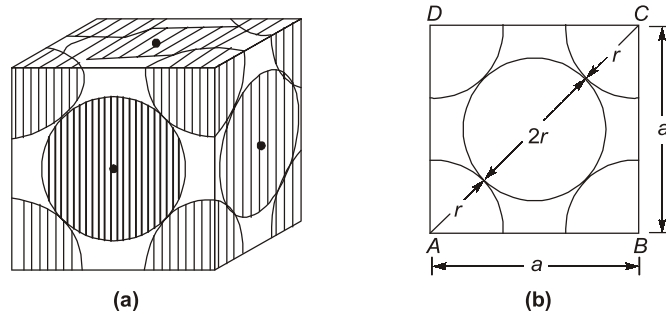
$$(\text{APF})_{\text{BCC}} = \frac{N \times \text{Volume of each sphere}}{\text{Total volume of each cell}}$$

$$= \frac{2 \times \frac{4}{3} \pi \left(\frac{a\sqrt{3}}{4} \right)^3}{a^3} = \frac{2 \times \pi\sqrt{3}}{16} a^3 = \frac{\pi\sqrt{3}}{8} = 0.68$$

\therefore % APF = 68% filled

- **Face Centered Cubic structure (FCC):**

In this structure, one atom lies at each corner of the cube in addition to one atom at the center of each face. The coordination number of FCC structure is $(4 + 4 + 4 = 12)$



Face centered cubic structure

From the figure,

$$\text{Radius of FCC} = r = \frac{a\sqrt{2}}{4}$$

and for FCC,

$$N = 4$$

Now,

$$(\text{APF})_{\text{FCC}} = \frac{N \times \text{Volume of each sphere}}{\text{Total volume of each cell}}$$

$$= \frac{4 \times \frac{4}{3} \pi \times \left(\frac{a\sqrt{2}}{4}\right)^3}{a^3} = \frac{4 \times \frac{\sqrt{2}\pi a^3}{24}}{a^3} = \frac{\sqrt{2}\pi}{6} = \frac{\pi}{3\sqrt{2}} = 0.74$$

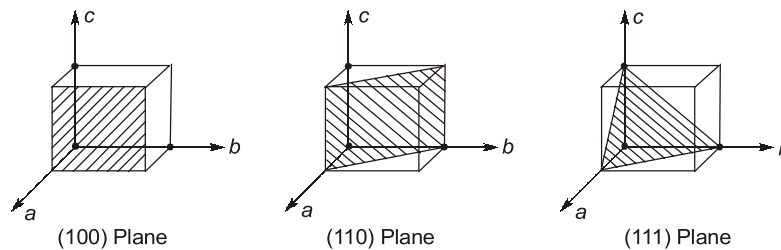
\therefore

$$\% \text{ APF} = 74 \% \text{ filled}$$

- 1.7 Draw sketches illustrating a (100) plane, a (110) plane, and a (111) plane in a cubic unit cell. How many equivalent (100) planes are there in a cubic crystal? A material has a face-centered cubic structure with an ionic radius of 1.06 Å. Calculate the interplanar separation for (111) planes.

(15 Marks)

Solution:



There are six equivalent (100) planes in a cubic crystal.

\Rightarrow In a face-centered cubic structure.

$$a\sqrt{2} = 4r$$

where

a = side of cube

r = ionic radius

Given : $r = 1.06 \text{ \AA}$

$$a = \frac{4r}{\sqrt{2}} = \frac{4 \times 1.06}{\sqrt{2}} = 2.998 \text{ \AA}$$

Interplanar separation for (111) planes is

$$d = \frac{a}{\sqrt{3}} = \frac{2.998}{\sqrt{3}} = 1.731 \text{ \AA}$$